



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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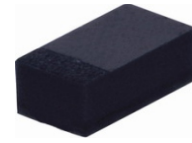
SMD Schottky Barrier Diode



SMD Diodes Specialist

CDBUR0145(RoHs Device)

$I_o = 100 \text{ mA}$
 $V_R = 45 \text{ Volts}$

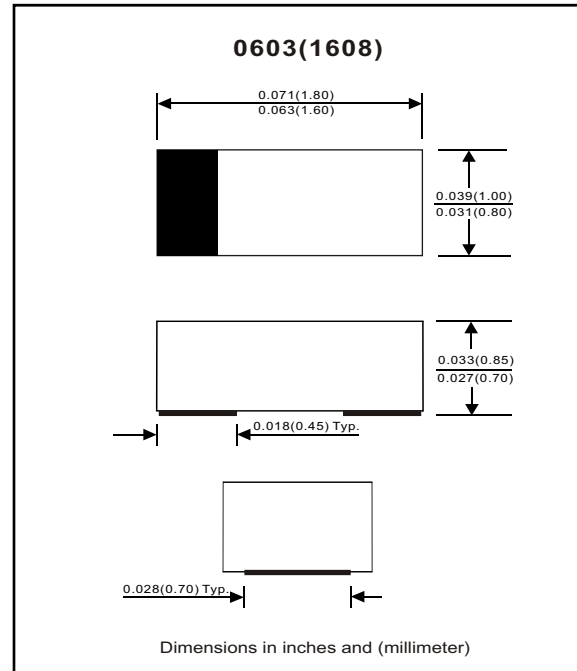


Features

- Designed for mounting on small surface.
- Extremely thin/leadless package.
- Low leakage current.
 $(I_R = 0.1 \mu\text{A typ. @ } V_R = 10\text{V})$
- Majority carrier conduction.

Mechanical data

- Case: 0603(1608) standard package, molded plastic.
- Terminals: Gold plated, solderable per MIL-STD-750, method 2026.
- Polarity: Indicated by cathode band.
- Mounting position: Any
- Weight: 0.003 gram(approx.).



Maximum Rating (at $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V_{RRM}			50	V
Reverse voltage		V_R			45	V
Average forward current		I_o			100	mA
Forward current, surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}		1000		mA
Power Dissipation		P_D			150	mW
Storage temperature		T_{STG}	-40		+125	$^\circ\text{C}$
Junction temperature		T_j			+125	$^\circ\text{C}$

Electrical Characteristics (at $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 100 \text{ mA DC}$	V_F			0.55	V
Reverse current	$V_R = 10\text{V}$	I_R			1	μA
Capacitance between terminals	$F = 1 \text{ MHz}$ and 10 VDC reverse voltage	C_T		9		pF

RATING AND CHARACTERISTIC CURVES (CDBUR0145)

Fig. 1 - Forward characteristics

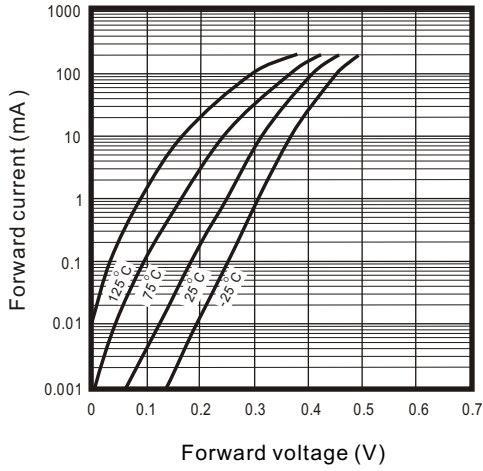


Fig. 2 - Reverse characteristics

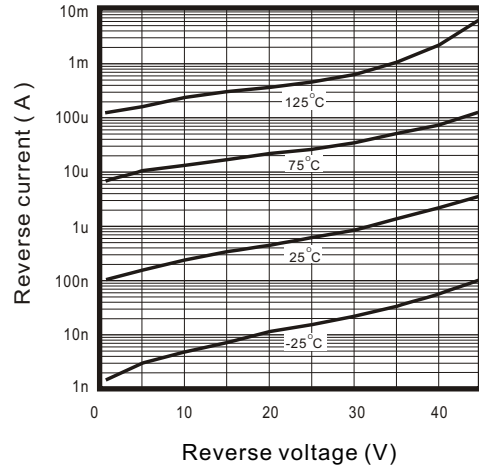


Fig.3 - Capacitance between terminals characteristics

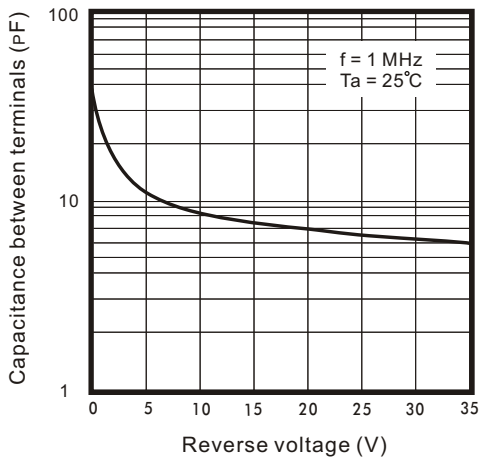


Fig.4 - Current derating curve

